

# Blue LED Chip

# SL-NBIT0320-[V#W#L#]

- MOVPE epi-wafer of InGaN alloy films
- Normal type chip (non-flip-chip)
- ※ All samples are 100% tested and sorted, and user can consult about special specifications.

### ■ ABSOLUTE MAXIMUM RATINGS ( Ta = 25 °C )

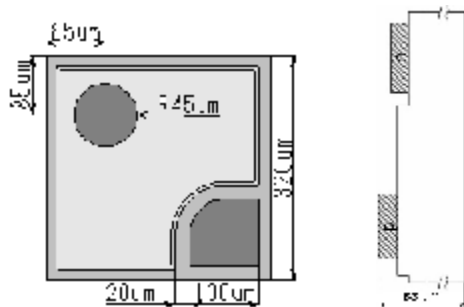
Item	Symbol	Maximum Rating	Unit
DC Forward Current	$I_F$	30	mA
Pulse Forward Current	$I_{FP}$	100	mA
Reverse Voltage	$V_R$	5	V
Operating Temperature	$T_{opr}$	-30 to +85	°C
Storage Temperature	$T_{stg}$	-40 to +100	°C
ESD sensitivity (HBM) *	$V_{ESDS}$	2000	V

\*ESD testing result is based on statistic measurements. Seller does not give assurance for every chip.

### ■ OPTICAL AND ELECTRICAL CHARACTERISTICS ( Ta = 25 °C )

Item	Symbol	Condition		Min	Typ	Max	Unit
Forward Voltage	$V_F$	$I_F=20mA$	$V_1$	2.8	2.9	3.0	V
			$V_2$	3.0	3.1	3.2	
			$V_3$	3.2	3.3	3.4	
Reverse Current	$I_R$	$V_R=5V$		-	-	1	μA
Wavelength	$\lambda_D$	$I_F=20mA$	$W_1$	465	-	467.5	nm
			$W_2$	467.5	-	470	
			$W_3$	470	-	472.5	
			$W_4$	472.5	-	475	
Luminous Intensity	$I_v$	$I_F=20mA$	$I_1$	80	-	90	mcd
			$I_2$	90	-	100	
			$I_3$	100	-	110	
			$I_4$	110	-	120	
			$I_5$	120	-	130	
			$I_6$	130	-	140	
			...	...	-	...	
			$I_{14}$	210	-	220	

### ■ CHIP DESCRIPTION



### ■ MECHANICAL SPECIFICATION

Description	Dimension
Emission Area	260 μm x 260 μm
Bottom Area	320 μm x 320 μm (±10 μm)
Chip Thickness	83 μm (±5 μm)
N-pad	Φ=100 μm
P-pad	Φ=90 μm
Electrodes Spacing	20 μm
Electrode material	AL